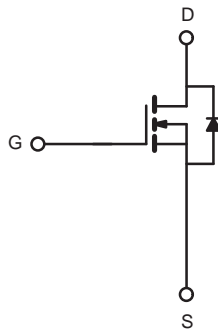
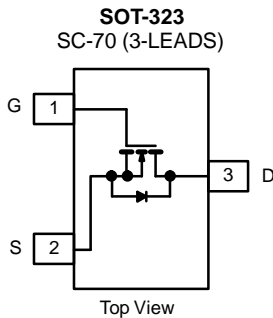


N-Channel 20 V (D-S) MOSFET

PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A) ^a	Q_g (Typ.)
20	0.036 at $V_{GS} = 10$ V	4	4 nC
	0.040 at $V_{GS} = 4.5$ V	3.8	
	0.048 at $V_{GS} = 2.5$ V	3.6	



FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- Typical ESD Protection 2000 V HBM
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Portable Devices
 - Load Switch
 - Battery Switch
- Load Switch for Motors, Relays and Solenoids

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	
Continuous Drain Current ($T_J = 150$ °C)	I_D	$T_C = 25$ °C	4 ^a
		$T_C = 70$ °C	3.6 ^a
		$T_A = 25$ °C	4 ^{a, b, c}
		$T_A = 70$ °C	3.7 ^{b, c}
Pulsed Drain Current ($t = 300$ μ s)	I_{DM}	20	A
Continuous Source-Drain Diode Current	I_S	$T_C = 25$ °C	
		$T_A = 25$ °C	1.3 ^{b, c}
Maximum Power Dissipation	P_D	$T_C = 25$ °C	2.8
		$T_C = 70$ °C	1.8
		$T_A = 25$ °C	1.56 ^{b, c}
		$T_A = 70$ °C	1.0 ^{b, c}
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	°C

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^{b, d}	R_{thJA}	60	80	°C/W
Maximum Junction-to-Foot (Drain)	R_{thJF}	34	45	

Notes:

- Package limited, $T_C = 25$ °C.
- Surface mounted on 1" x 1" FR4 board.
- $t = 5$ s.
- Maximum under steady state conditions is 125 °C/W.

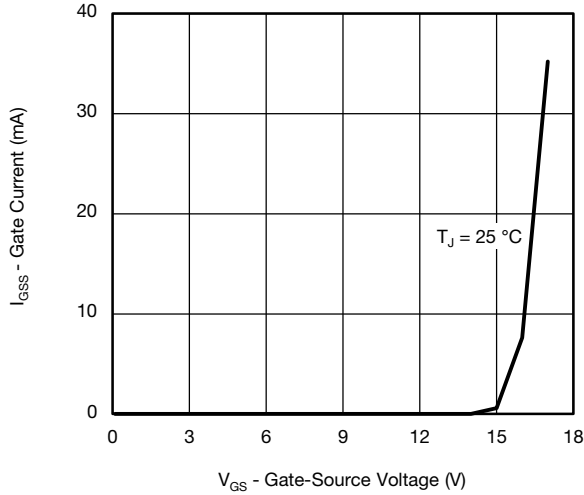
SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	20			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		23		mV/ $^\circ\text{C}$
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			-3.2		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	0.6		1.3	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 4.5\text{ V}$			± 0.5	μA
		$V_{DS} = 0\text{ V}, V_{GS} = \pm 12\text{ V}$			± 25	
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}$			1	
		$V_{DS} = 20\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 4.5\text{ V}$	15			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 3.7\text{ A}$		0.036		Ω
		$V_{GS} = 4.5\text{ V}, I_D = 3.6\text{ A}$		0.040		
		$V_{GS} = 2.5\text{ V}, I_D = 1.5\text{ A}$		0.048		
Forward Transconductance ^a	g_{fs}	$V_{DS} = 15\text{ V}, I_D = 3.7\text{ A}$		17		S
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = 15\text{ V}, V_{GS} = 10\text{ V}, I_D = 3.7\text{ A}$		8.8	13.5	nC
		$V_{DS} = 15\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 3.7\text{ A}$		4	6	
Gate-Source Charge	Q_{gs}			0.9		
Gate-Drain Charge	Q_{gd}		1.1			
Gate Resistance	R_g	$f = 1\text{ MHz}$	0.4	2	4	$\text{k}\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 4.1\text{ }\Omega$ $I_D \approx 3.7\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$		0.29	0.58	μs
Rise Time	t_r			0.4	0.8	
Turn-Off Delay Time	$t_{d(off)}$			1.9	3.8	
Fall Time	t_f			0.75	1.5	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 15\text{ V}, R_L = 4.1\text{ }\Omega$ $I_D \approx 3.7\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		0.1	0.2	
Rise Time	t_r			0.15	0.3	
Turn-Off Delay Time	$t_{d(off)}$			3	6	
Fall Time	t_f			0.75	1.5	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			2.3	A
Pulse Diode Forward Current	I_{SM}				20	
Body Diode Voltage	V_{SD}	$I_S = 3.7\text{ A}, V_{GS} = 0\text{ V}$		0.85	1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = 3.7\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		12	25	ns
Body Diode Reverse Recovery Charge	Q_{rr}			5	10	nC
Reverse Recovery Fall Time	t_a			6.5		ns
Reverse Recovery Rise Time	t_b			5.5		

Notes:

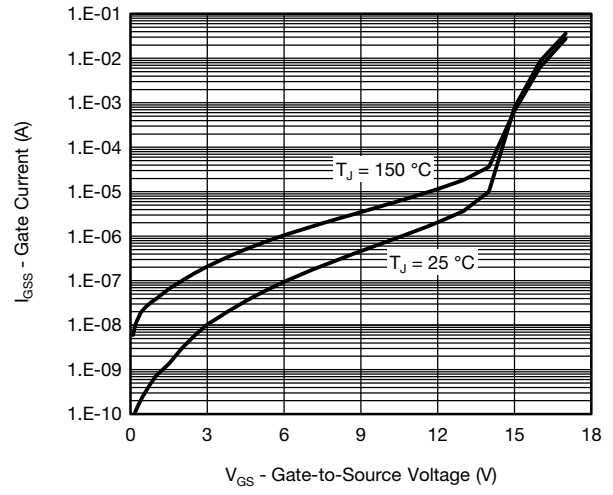
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

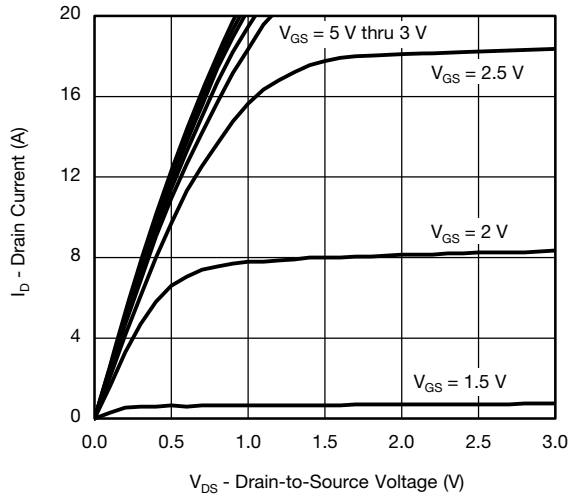
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



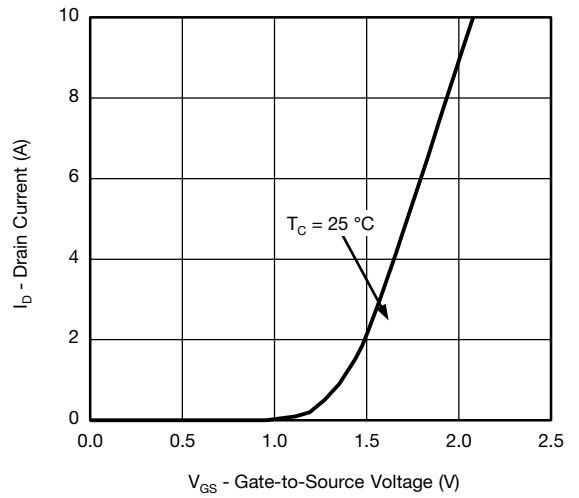
Gate Current vs. Gate-to-Source Voltage



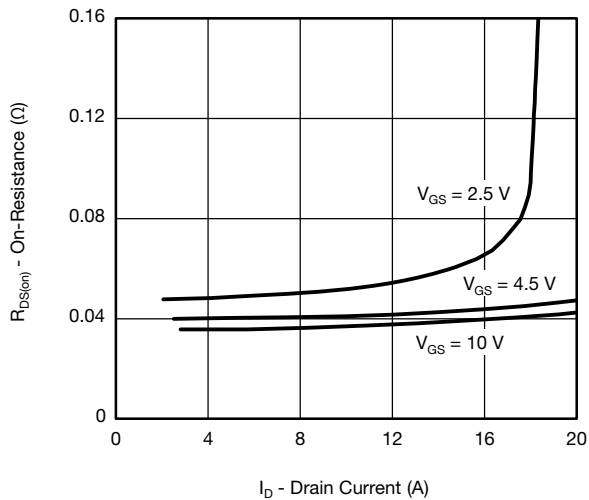
Gate Current vs. Gate-to-Source Voltage



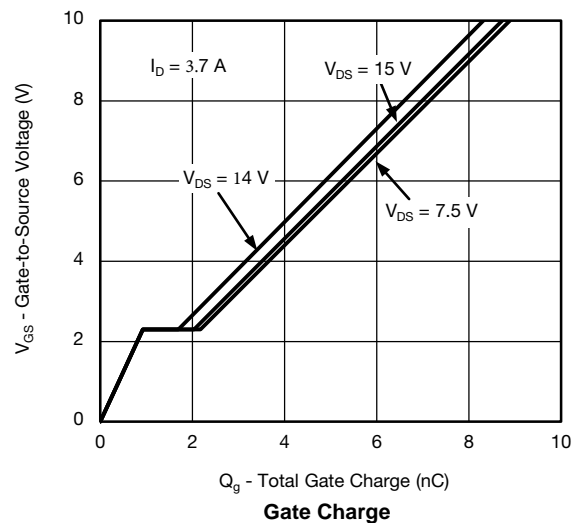
Output Characteristics



Transfer Characteristics

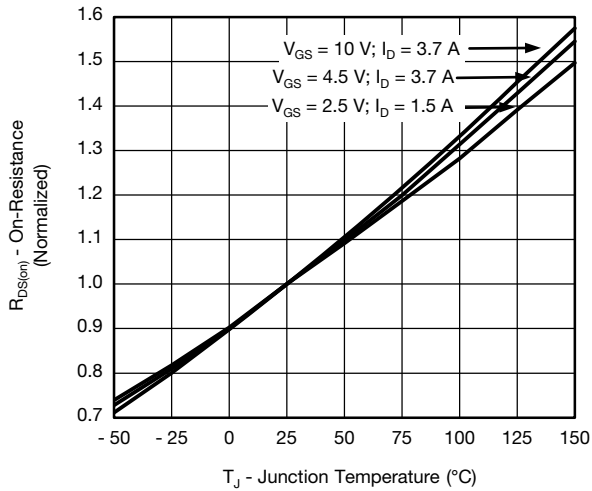


On-Resistance vs. Drain Current

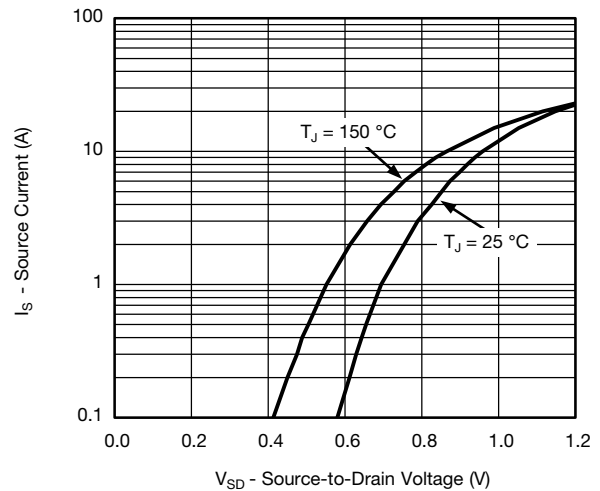


Gate Charge

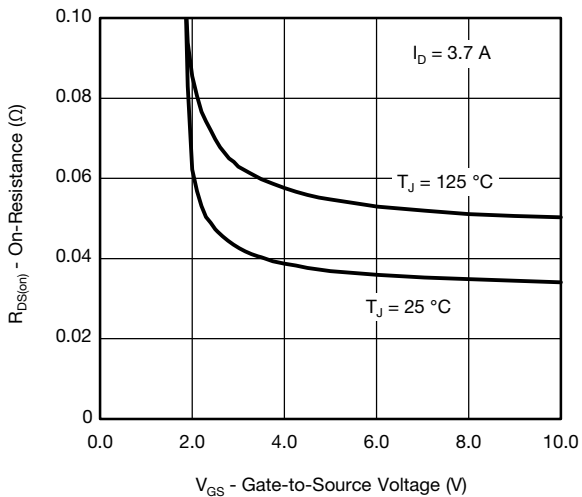
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



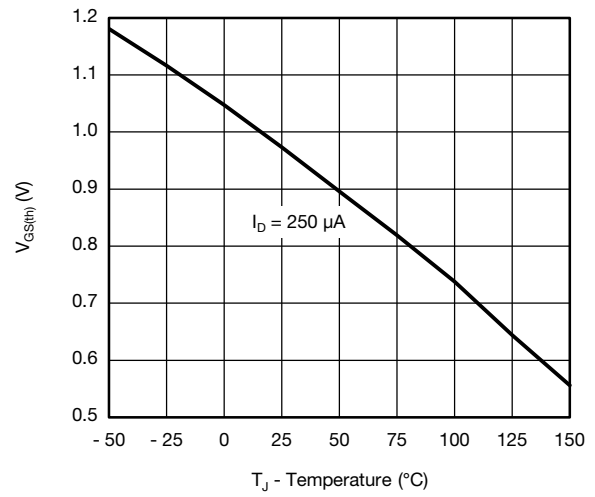
Normalized On-Resistance vs. Junction Temperature



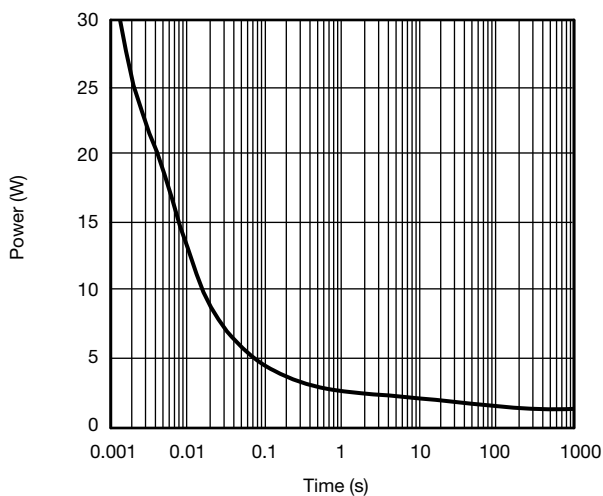
Source-Drain Diode Forward Voltage



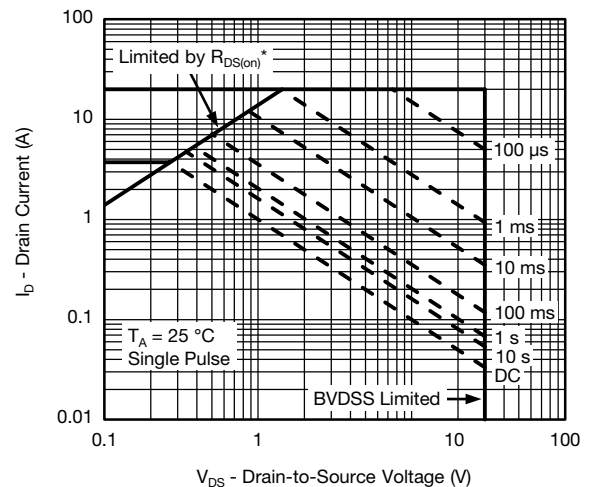
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

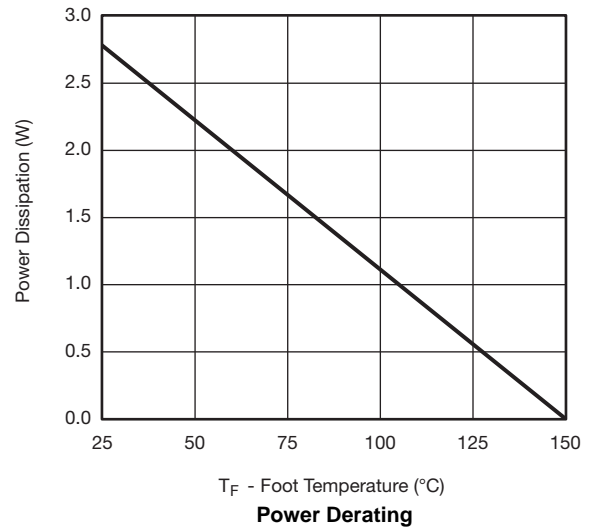


Single Pulse Power, Junction-to-Ambient



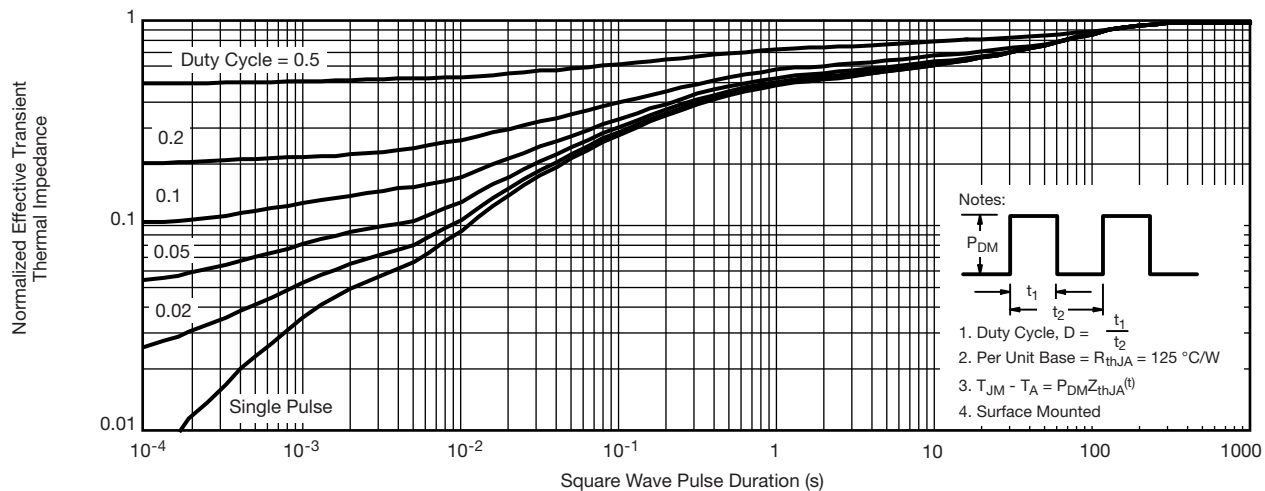
Safe Operating Area, Junction-to-Ambient
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)

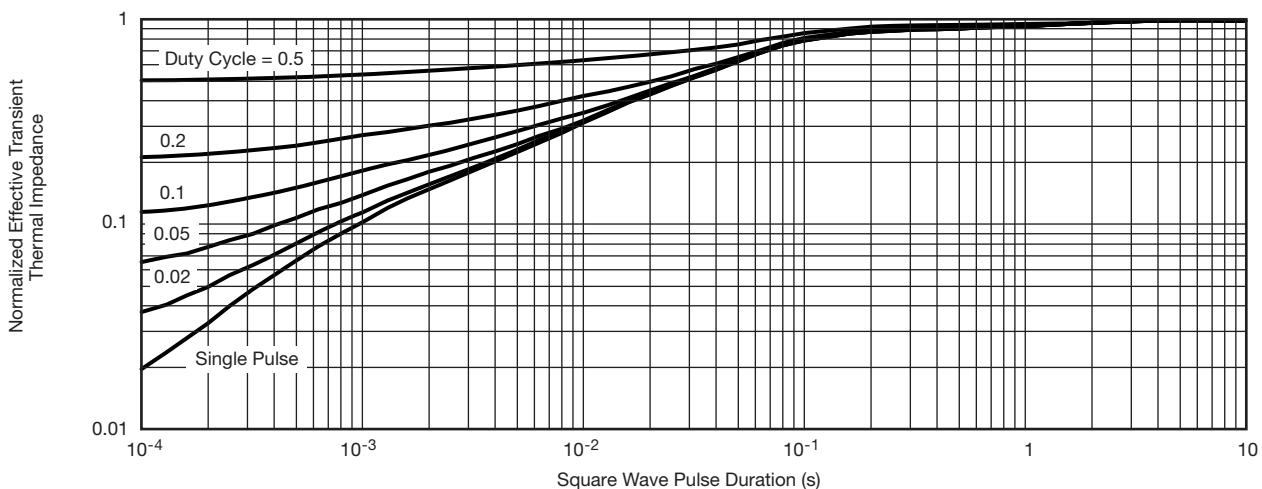


* The power dissipation P_D is based on $T_{J(max)} = 150\text{ }^\circ\text{C}$, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

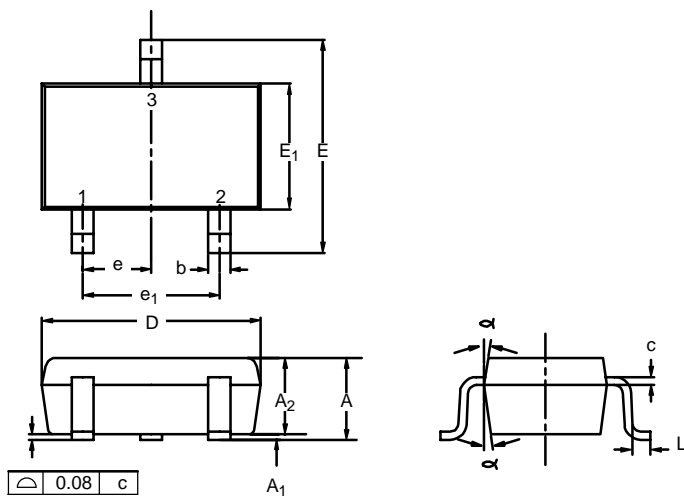
TYPICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient

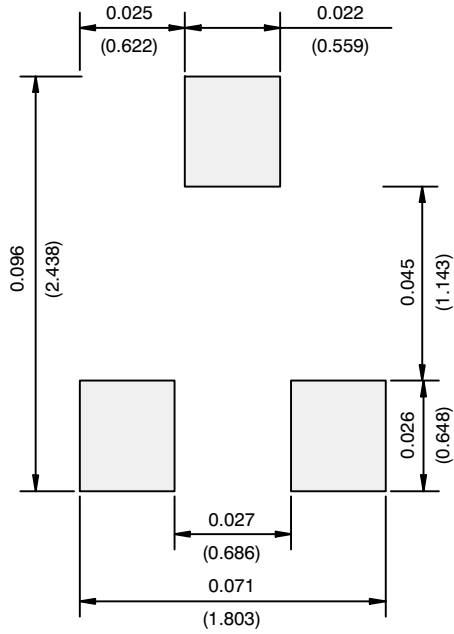


Normalized Thermal Transient Impedance, Junction-to-Foot

SC-70: 3-LEADS

Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.90	–	1.10	0.035	–	0.043
A₁	–	–	0.10	–	–	0.004
A₂	0.80	–	1.00	0.031	–	0.039
b	0.25	–	0.40	0.010	–	0.016
c	0.10	–	0.25	0.004	–	0.010
D	1.80	2.00	2.20	0.071	0.079	0.087
E	1.80	2.10	2.40	0.071	0.083	0.094
E₁	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65BSC			0.026BSC		
e₁	1.20	1.30	1.40	0.047	0.051	0.055
L	0.10	0.20	0.30	0.004	0.008	0.012
α	7°Nom			7°Nom		
ECN: S-03946—Rev. C, 09-Jul-01 DWG: 5549						

RECOMMENDED MINIMUM PADS FOR SC-70: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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